MJ P-Channel Enhancement Mode Power MOSFET

Description

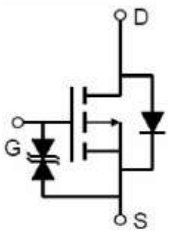
The MJ01P30K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protested.

General Features

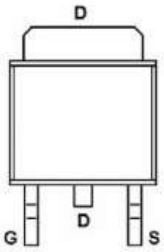
- ◆ V_{DS} =-100V,I_D =-30A
  $R_{DS(ON)}$ <58mΩ @ V_{GS}=-10V (Typ:44mΩ)
  $R_{DS(ON)}$ <65mΩ @ V_{GS}=-4.5V (Typ:48mΩ)
- ◆ Super high dense cell design
- ◆ Advanced trench process technology
- ◆ Reliable and rugged
- ◆ High density celldesign for ultra low on-resistance

Application

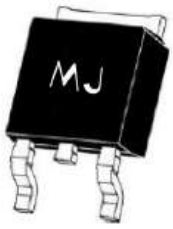
- ◆ Portable equipment and battery powered systems



Schematic diagram



Marking and pin assignment



TO-252-2L top view

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJ01P30K	MJ01P30K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C =25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-30	A
Drain Current-Continuous(T_C =100℃)	$I_{D(100℃)}$	-21	A
Pulsed Drain Current	I_{DM}	-150	A
Maximum Power Dissipation	P_D	120	W
Derating factor		0.8	W/℃
Operating Junction and Storage Temperature Range	T_J ,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	1.25	℃/W

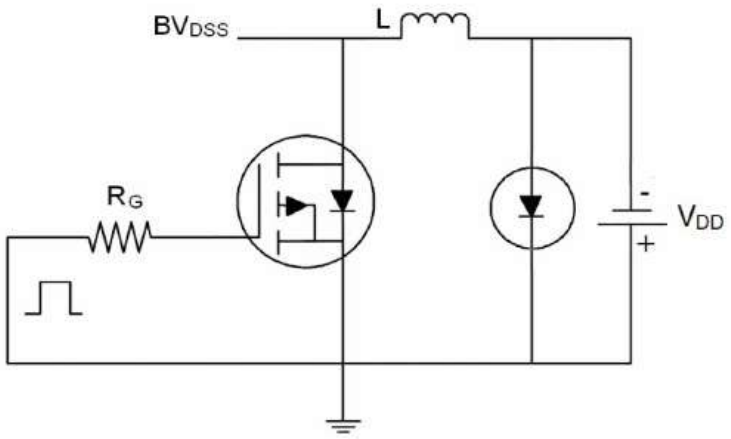
Electrical Characteristics (T_C =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=±20V,V_{DS}=0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} ,I_D=-250μA	-1.5	-1.9	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-15A	-	44	58	mΩ
		V_{GS}=-4.5V, I_D=-15A	-	48	65	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-50V,I_D=-10A	5	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{lss}	V_{DS}=-50V,V_{GS}=0V, F=1.0MHz	-	3810	-	PF
Output Capacitance	C_{oss}		-	93	-	PF
Reverse Transfer Capacitance	C_{rss}		-	91	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-50V,I_D=-15A V_{GS}=-10V,R_{GEN}=9.1Ω	-	17	-	nS
Turn-on Rise Time	t_r		-	80	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	nS
Turn-Off Fall Time	t_f		-	65	-	nS
Total Gate Charge	Q_g	V_{DS}=-50V,I_D=-15A V_{GS}=-10V	-	136	-	nC
Gate-Source Charge	Q_{gs}		-	22	-	nC
Gate-Drain Charge	Q_{gd}		-	26	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-10A	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-30	A
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=-15A di/dt=100A/μs (Note 3)	-	90	-	nS
Reverse Recovery Charge	Q_{rr}		-	70	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible(turn-on is dominated by LS+LD)				

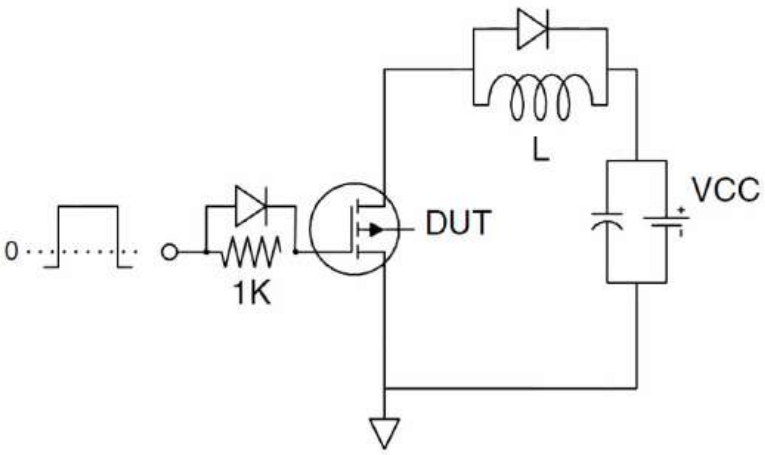
Notes:

① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t ≤ 10 sec.
③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
④ Guaranteed by design, not subject to production

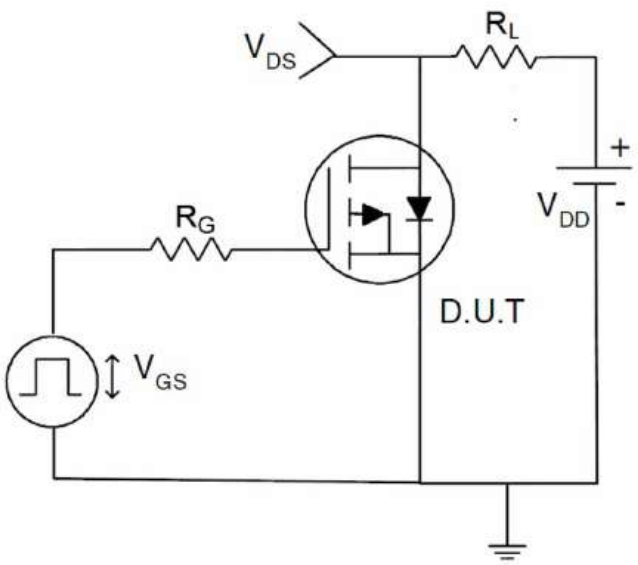
Test circuit



EAS test Circuit

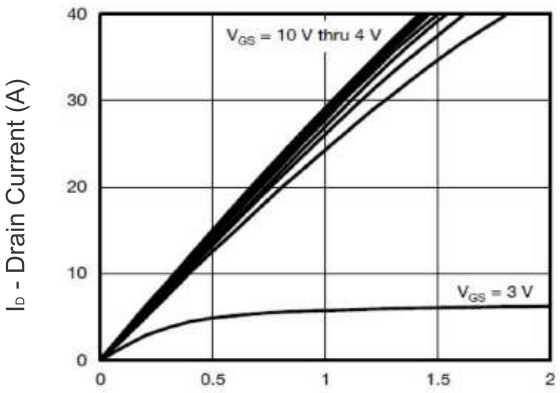


Gate charge test Circuit



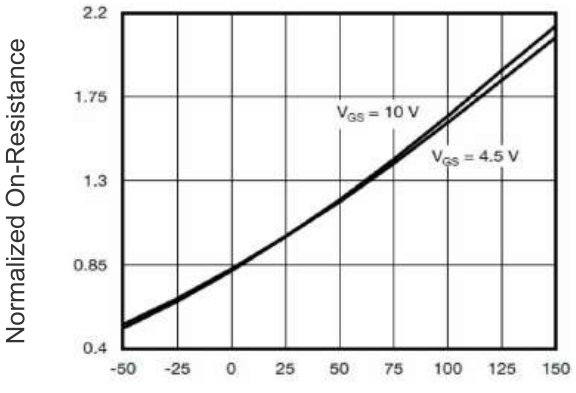
Switch Time Test Circuit

Typical Electrical and Thermal Characteristics (Curves)



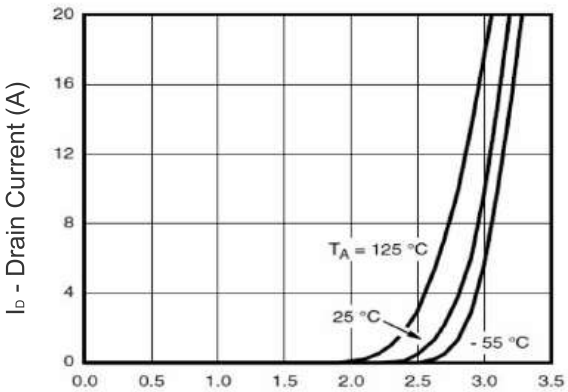
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



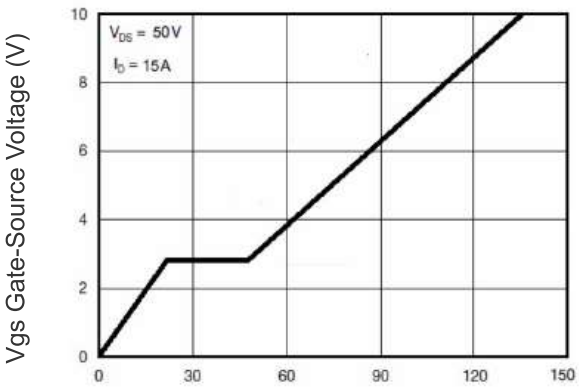
T_J -Junction Temperature(℃)

Figure 4 Rdson-Junction Temperature



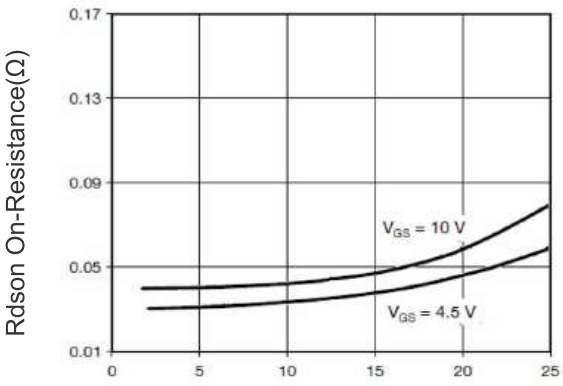
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



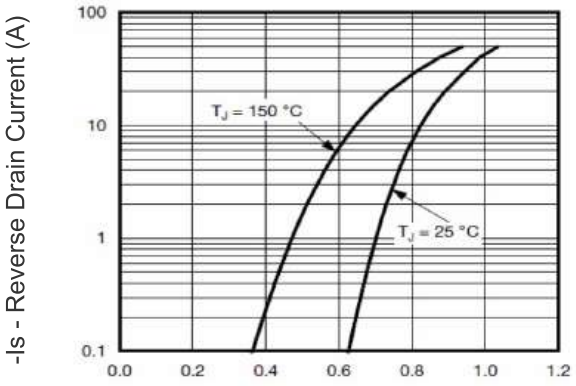
Qg Gate Charge (nC)

Figure 5 Gate Charge



$-I_D$ - Drain Current (A)

Figure 3 Rdson- Drain Current



-Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

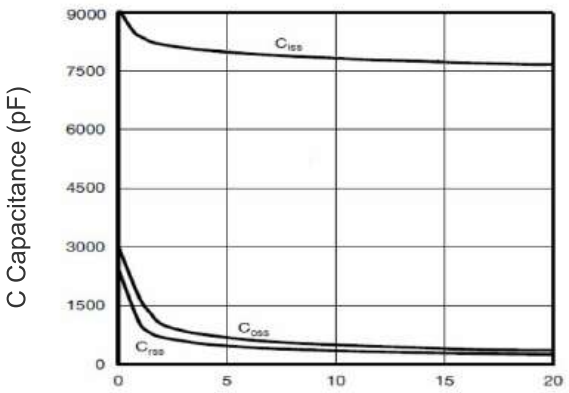


Figure 7 Capacitance vs Vds

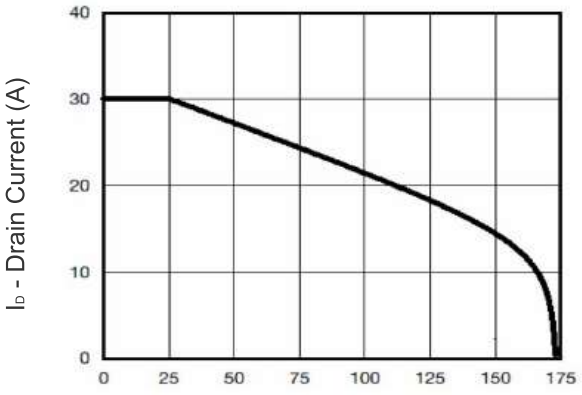


Figure 9 Drain Current vs Case Temperature

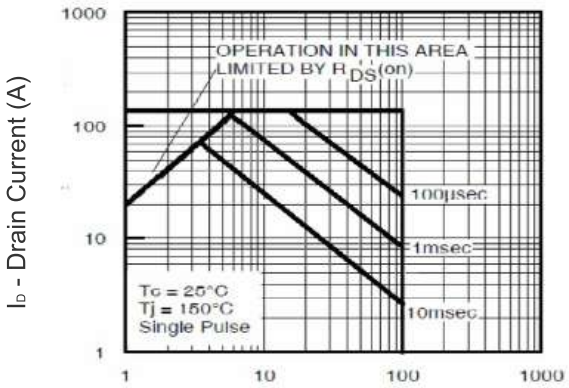


Figure 8 Safe Operation Area

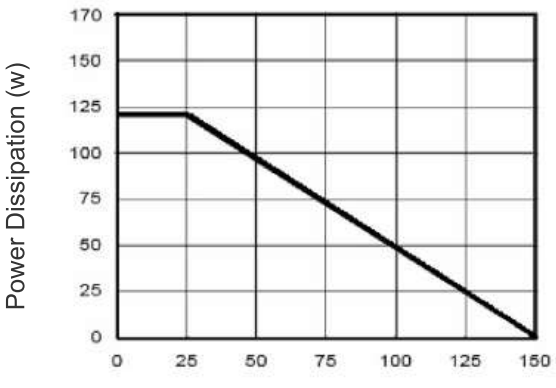


Figure 10 Power De-rating

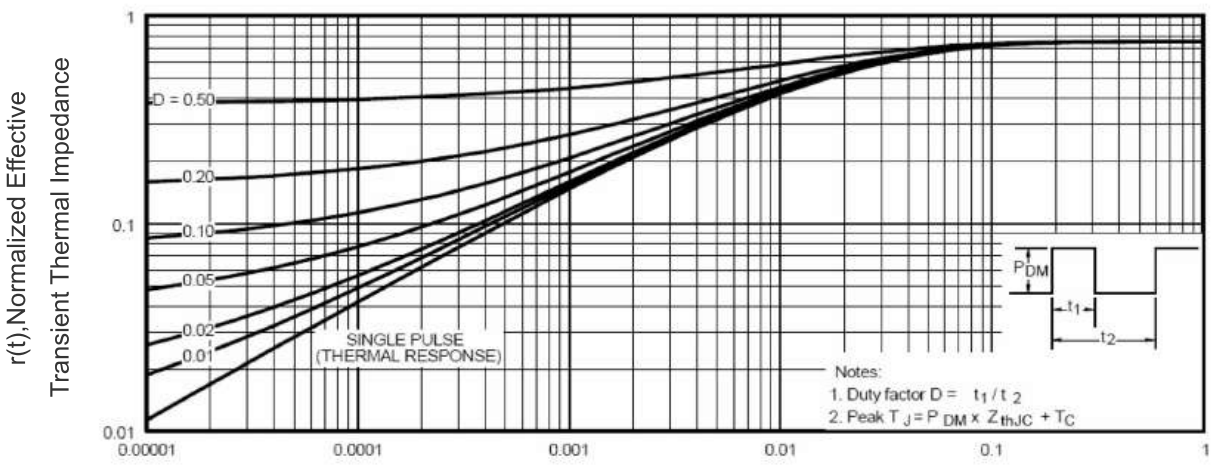
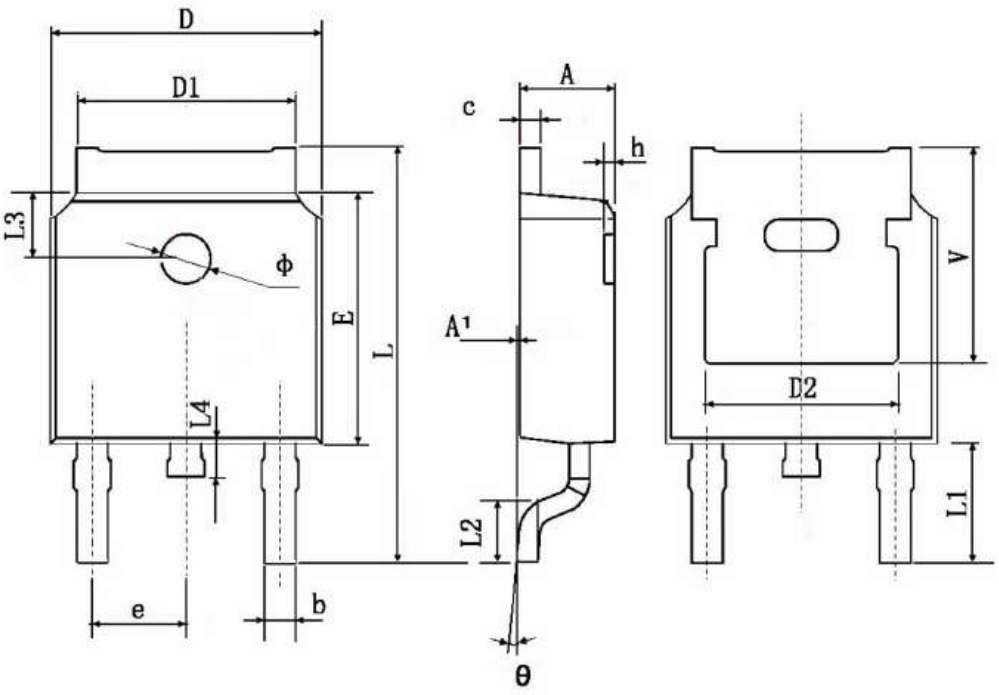


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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